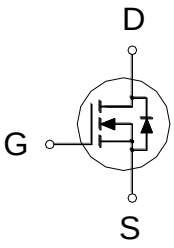
NIKO-SEM

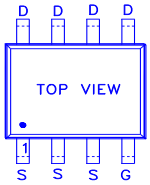
N-Channel Enhancement Mode Field Effect Transistor

PV6A4BA
SOP-8
Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	14mΩ	7.8A





G: GATE
D: DRAIN
S: SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 ° C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 ° C	I_D	7.8	A
	T_A = 70 ° C		6.2	
Pulsed Drain Current[1]		I_{DM}	30	
Avalanche Current		I_{AS}	20	
Avalanche Energy	L = 0.1mH	E_{AS}	20	mJ
Power Dissipation	T_A = 25 ° C	P_D	1.8	W
	T_A = 70 ° C		1.1	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	° C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		69	° C / W
Junction-to-Case	$R_{\theta JC}$		25	

[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C.

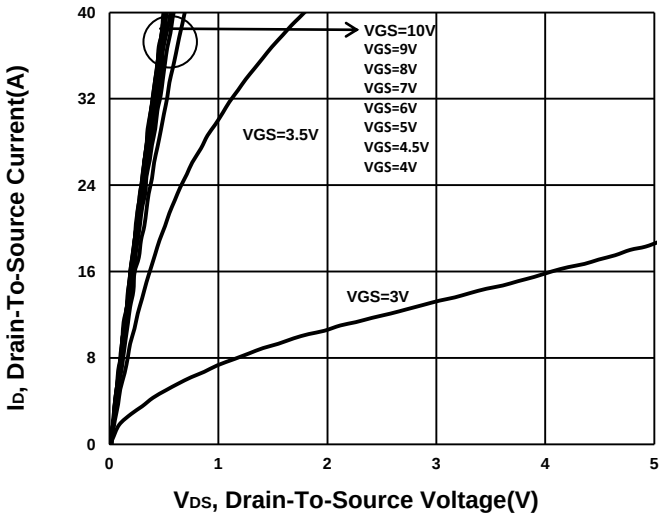
.ELECTRICAL CHARACTERISTICS (T_J = 25 ° C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.7	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 32V, V_{GS} = 0V			1	μA
		V_{DS} = 30V, V_{GS} = 0V, T_J = 55 ° C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 7.8A		10	14	mΩ
		V_{GS} =4.5V, I_D = 7.8A		12	20	

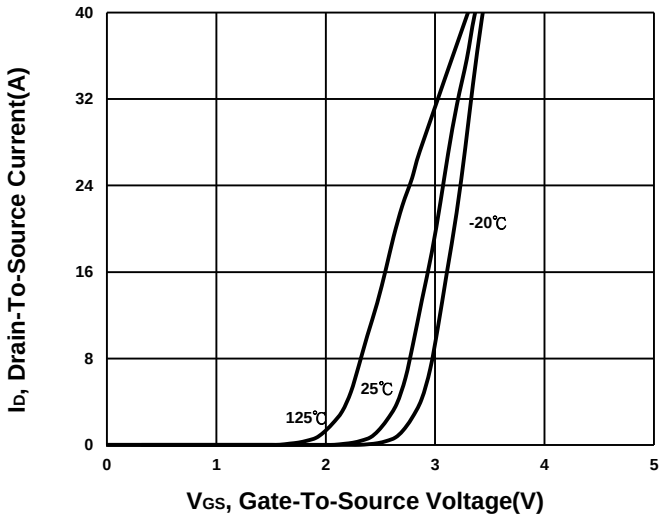
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 10A		50		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz		853		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			63		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2.5		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 20V , I_D = 7.8A		17		nC
	$Q_{g(VGS=4.5V)}$			9		
Gate-Source Charge[2]	Q_{gs}			2.5		
Gate-Drain Charge[2]	Q_{gd}			4.3		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 20V , $I_D \cong$ 7.8A, V_{GS} = 10V, R_{GEN} = 6Ω		15		nS
Rise Time[2]	t_r			11		
Turn-Off Delay Time[2]	$t_{d(off)}$			32		
Fall Time[2]	t_f			12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 ° C)						
Continuous Current	I_S				1.4	A
Forward Voltage[1]	V_{SD}	I_F = 7.8A, V_{GS} = 0V			1.3	V
Diode Reverse Recovery Time	t_{rr}	I_F= 7.8A, dI/dt= 100A/μs		14		nS
Diode Reverse Recovery Charge	Q_{rr}			4.6		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

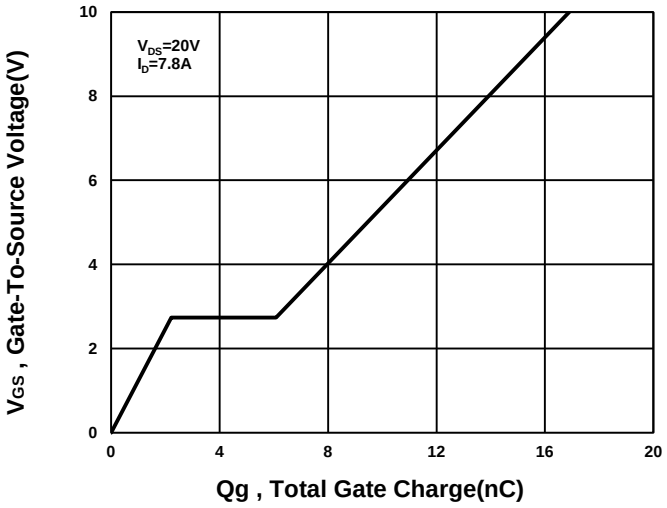
Output Characteristics



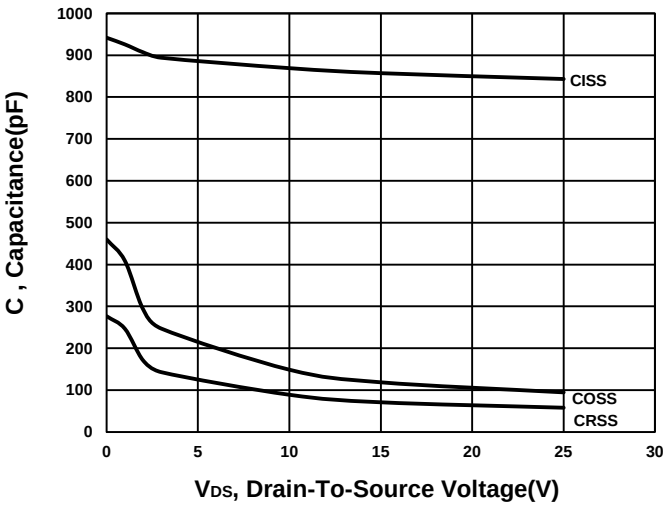
Transfer Characteristics



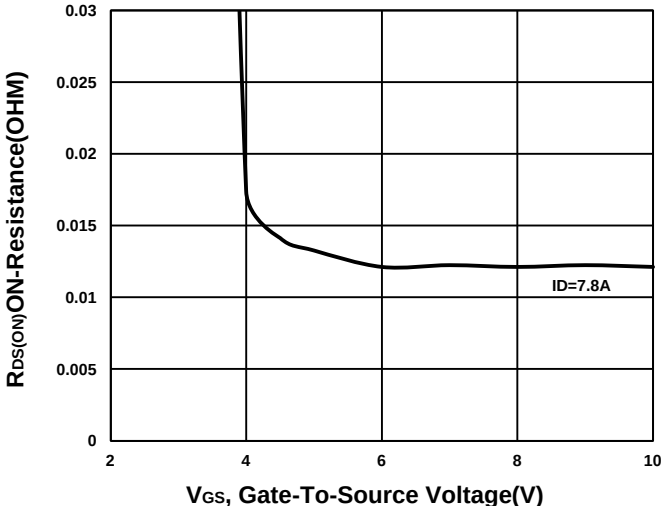
Gate charge Characteristics



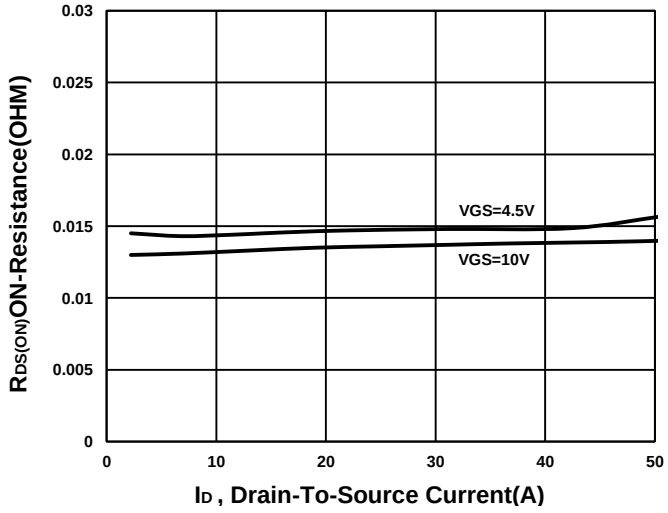
Capacitance Characteristic



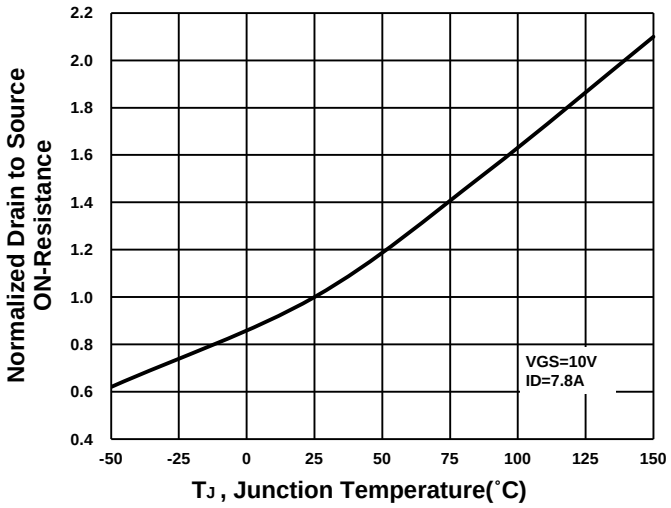
On-Resistance VS Gate-To-Source



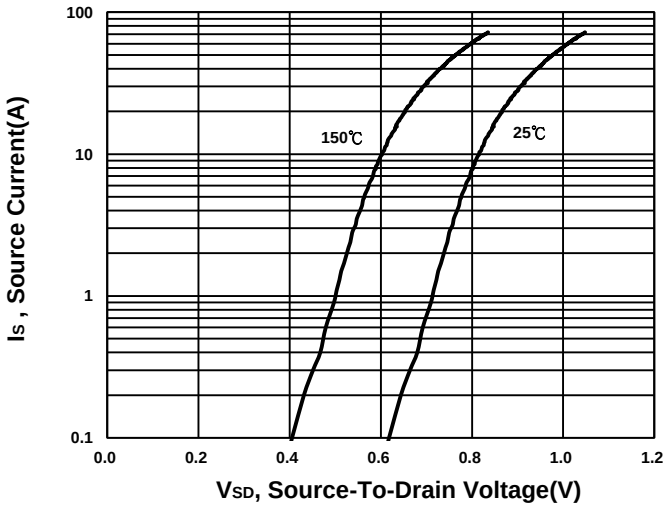
On-Resistance VS Drain Current



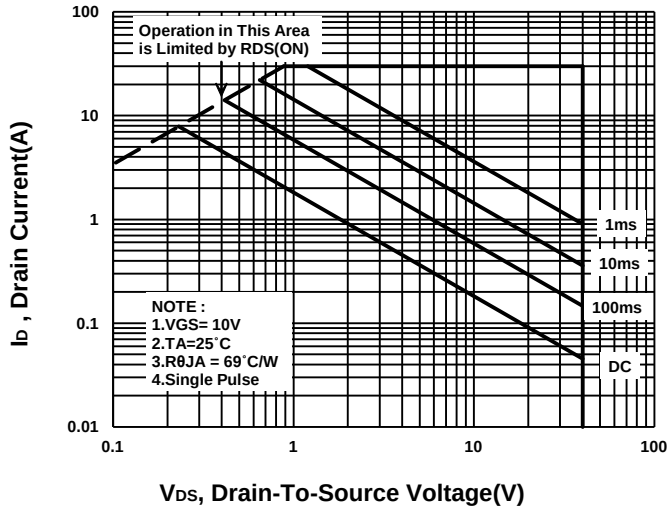
On-Resistance VS Temperature



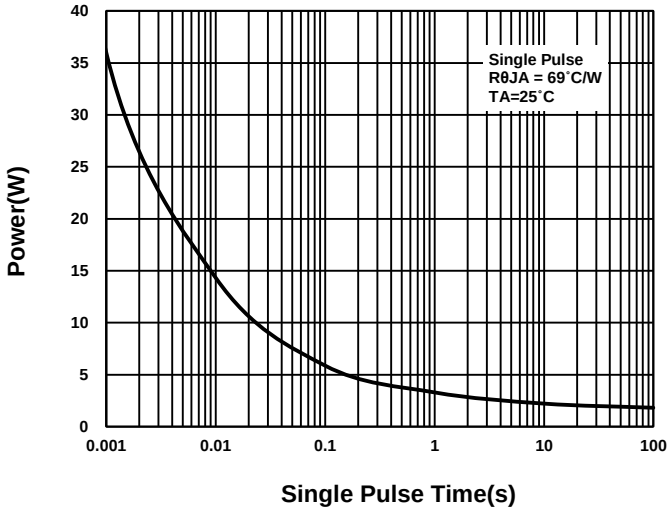
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve